

STGW50HF60S

60 A, 600 V, very low drop IGBT

Features

- Very low on-state voltage drop
- Low switching off
- High current capability

Applications

- PV inverter
- UPS

Description

STGW50HF60S is a very low drop IGBT based on new advanced planar technology, showing extremely low on-state voltage and limited turn-off losses. The overall performance makes this IGBT ideal in low frequency switches of mixed frequency topologies for PF \leq 1.

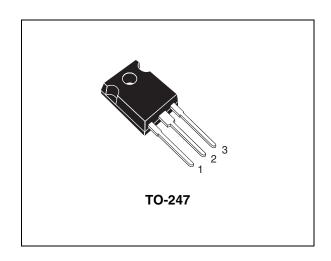


Figure 1. Internal schematic diagram

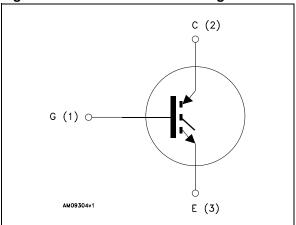


Table 1. Device summary

Order code	Marking	Package	Packaging
STGW50HF60S	STGW50HF60S GW50HF60S		Tube

Electrical ratings STGW50HF60S

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	600	V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	110	Α
I _C ⁽¹⁾	Continuous collector current at T _C = 100 °C	60	Α
I _{CL} ⁽²⁾	Turn-off latching current	60	Α
I _{CP} (3)	Pulsed collector current	130	Α
V_{GE}	Gate-emitter voltage	±20	٧
P _{TOT}	Total dissipation at T _C = 25 °C	284	W
T _j	Operating junction temperature	- 55 to 150	°C

^{1.} Calculated according to the iterative formula:

$$I_{C}(T_{C}) = \frac{T_{j(max)} - T_{C}}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_{C}(T_{C}))}$$

- 2. Vclamp = 80% of V_{CES}, T_j =150 °C, R_G=10 Ω , V_{GE}=15 V
- 3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case	0.44	°C/W
R _{thJA}	Thermal resistance junction-ambient	50	°C/W

2 Electrical characteristics

 $T_J = 25~^{\circ}C$ unless otherwise specified.

Table 4. Static

Symbol	ool Parameter Test conditions		Min.	Тур.	Max.	Unit
V _{(BR)CES}	Collector-emitter breakdown voltage (V _{GE} = 0)	I _C = 1 mA	600			٧
V _{CE(sat)}	Collector-emitter saturation voltage	V_{GE} = 15 V, I_{C} = 30 A V_{GE} = 15 V, I_{C} = 30 A, T_{J} =125 °C		1.15	1.45	< <
V _{GE(th)}	Gate threshold voltage	V _{CE} = V _{GE} , I _C = 250 μA	3.5		5.7	V
I _{CES}	Collector cut-off current (V _{GE} = 0)	V _{CE} =600 V V _{CE} =600 V, T _J =125 °C			50 500	μ Α μ Α
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	V _{GE} =± 20 V			± 100	nA
9 _{fs}	Forward transconductance	V _{CE} = 15 V _, I _C = 30 A		25		S

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} =0	-	4300 400 100	-	pF pF pF
Q _g Q _{ge} Q _{gc}	Total gate charge Gate-emitter charge Gate-collector charge	V _{CE} = 480 V, I _C = 30 A,V _{GE} =15 V	1	200 27 90	1	nC nC nC

Electrical characteristics STGW50HF60S

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 400 V, I_{C} = 30 A R_{G} = 10 Ω , V_{GE} = 15 V, (see Figure 14)	-	50 20 1280	-	ns ns A/µs
t _{d(on)} t _r (di/dt) _{on}	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 400 \text{ V}, I_{C} = 30 \text{ A}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_{J} = 125 \text{ °C} \text{ (see Figure 14)}$	-	47 22 1100	-	ns ns A/µs
$\begin{array}{c} t_{r}(V_{off}) \\ t_{d}(_{off}) \\ t_{f} \end{array}$	Off voltage rise time Turn-off delay time Current fall time	V_{CC} = 400 V, I_{C} = 30 A R_{G} = 10 Ω , V_{GE} = 15 V, (see Figure 14)	1	370 220 465	1	ns ns ns
$t_r(V_{off})$ $t_d(_{off})$ t_f	Off voltage rise time Turn-off delay time Current fall time	$V_{CC} = 400 \text{ V}, I_{C} = 30 \text{ A}$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ $T_{J} = 125 ^{\circ}\text{C}$ (see Figure 14)	-	700 250 800	-	ns ns ns

Table 7. Switching energy (inductive load)

		<u> </u>				
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Eon (1)	Turn-on switching losses	$V_{CC} = 400 \text{ V}, I_{C} = 30 \text{ A}$		0.25		mJ
E _{off} (2)	Turn-off switching losses	R_{G} = 10 Ω , V_{GE} = 15 V,	-	4.2	-	mJ
E _{ts}	Total switching losses	(see Figure 14)		4.45		mJ
Eon ⁽¹⁾	Turn-on switching losses	$V_{CC} = 400 \text{ V}, I_{C} = 30 \text{ A}$		0.45		mJ
E _{off} (2)	Turn-off switching losses	R_G = 10 Ω , V_{GE} = 15 V ,	-	7.8	-	mJ
E _{ts}	Total switching losses	T _J = 125 °C <i>(see Figure 14)</i>		8.25		mJ

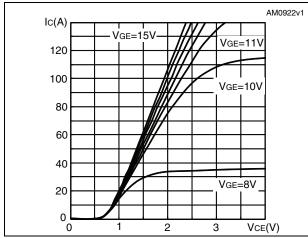
Eon is the turn-on losses when a typical diode is used in the test circuit in *Figure 14*. If the IGBT is offered
in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs and diode are at the
same temperature (25 °C and 125 °C).

^{2.} Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

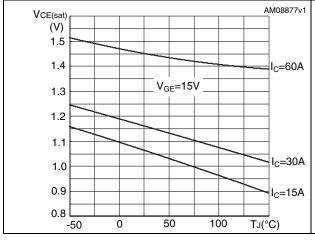
Figure 3. Transfer characteristics



IC(A)
120
100
80
60
40
20
0 2 4 6 8 10 VGE(V)

Figure 4. Collector-emitter on voltage vs. temperature

Figure 5. Collector-emitter on voltage vs. collector current



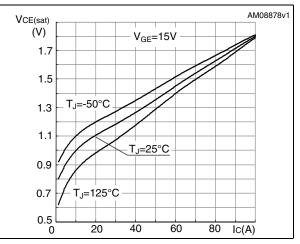
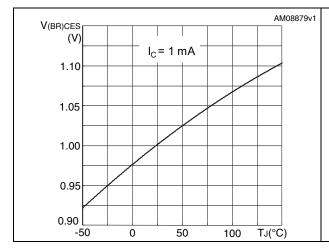
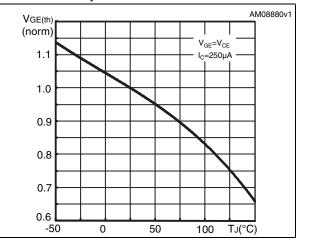


Figure 6. Breakdown voltage vs. temperature Figure 7. Gate threshold voltage vs. temperature

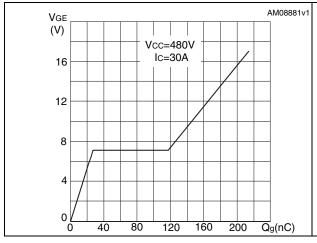




Electrical characteristics STGW50HF60S

Figure 8. Gate charge vs. gate-emitter voltage

Figure 9. Capacitance variations



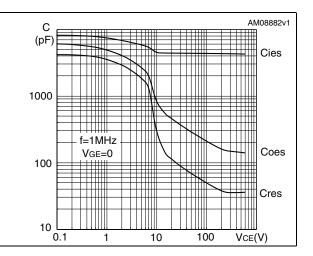
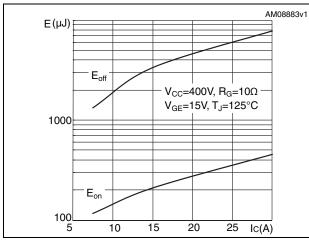


Figure 10. Switching losses vs. collector current

Figure 11. Switching losses vs. gate resistance



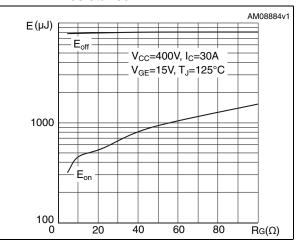
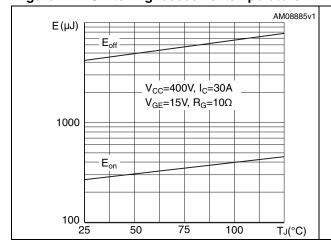
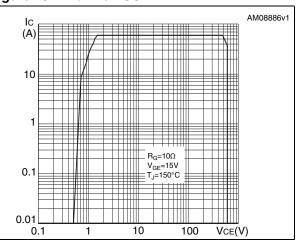


Figure 12. Switching losses vs. temperature

Figure 13. Turn-off SOA





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STGW50HF60S Test circuits

3 Test circuits

Figure 14. Test circuit for inductive load switching

Figure 15. Gate charge test circuit

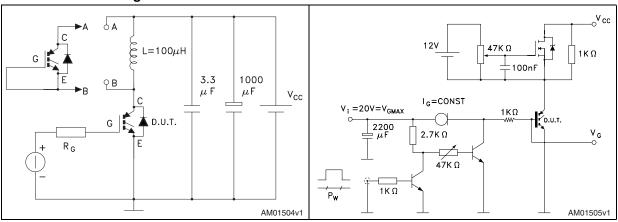
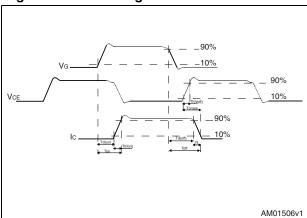


Figure 16. Switching waveform



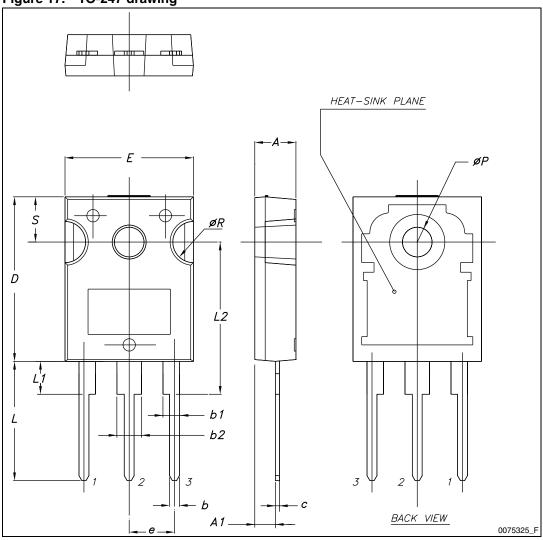
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. TO-247 mechanical data

Dim.		mm	
Dilli.	Min.	Тур.	Max.
Α	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
С	0.40		0.80
D	19.85		20.15
E	15.45		15.75
е		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 17. TO-247 drawing



Revision history STGW50HF60S

5 Revision history

Table 9. Document revision history

Date	Revision	Changes
18-Jan-2010	1	Initial release.
21-Jan-2011	2	Document status promoted from preliminary data to datasheet.

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